TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA2008AN

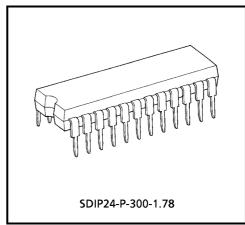
5V AM / FM 1 Chip Tuner IC (for digital tuning system)

The TA2008AN is the AM / FM 1 chip tuner IC, which is designed for radio cassette players and music centers.

This is suitable for digital tuning system applications.

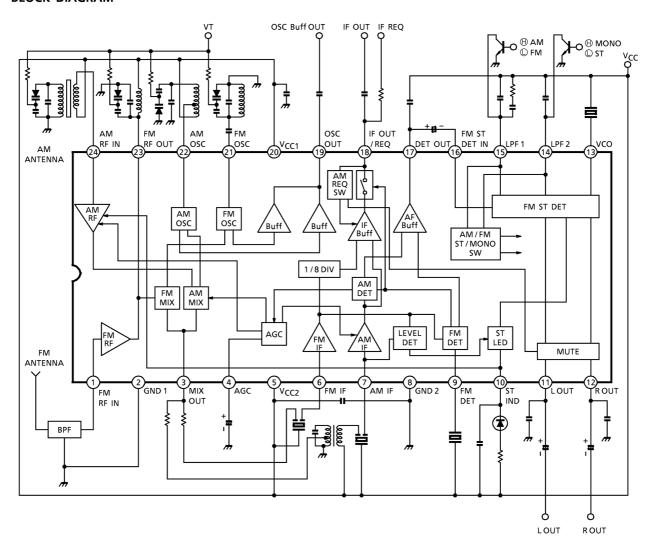
Features

- Suitable for combination with digital tuning system which is included IF counter.
- One terminal type AM / FM IF count output (auto stop signal) for IF counter of digital tuning system.
 - FM: 1.3375MHz (1 / 8 dividing)
 - AM: 450kHz
- Built-in mute circuit for IF count output.
- For adopting ceramic discriminator and ceramic resonator, it is not necessary to adjust the FM quad detector circuit and FM stereo detector vco circuit.
- Built-in one terminal type AM / FM local oscillator buffer output for digital tuning system applications.
- Operating supply voltage range: $V_{CC} = 3.5 \sim 14V$ (Ta = 25°C)



Weight: 1.2g (typ.)

BLOCK DIAGRAM



Explanation Of Terminals

Pin	Characteristic Internal Circ	Internal Circuit	DC Volt (at no	tage (V) signal)
No.			AM	FM
1	FM-RF in	FM-RF OUT 23 4 4 6 GND1 2	0	0.8
2	GND1 (GND for RF stage)	_	0	0
3	Mix out	VCC1 20 AM MIX FM MIX GND1 2 3	0.3	0.8
4	AGC	V _{CC2} (S)	1.2	0.9
5	V _{CC2} (V _{CC} for IF / FM ST DET stage)	_	5.0	5.0
6	FM IF in	VCC2 (5) CO E E E E E E E E E E E E E E E E E E	5.0	5.0

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
NO.			AM	FM	
7	AM IF in	VCC2 S C MAN TO THE STATE OF TH	5.0	5.0	
8	GND2 (GND for if / FM ST DET stage)	_	0	0	
9	QUAD (FM QUAD. Detector)	V _{CC2} 5 9 GND2 8	4.1	3.6	
10	St ind • Stereo LED terminal • Offset voltage cancel for AM RF amp.	19kHz AM RF Amp	4.2	_	
11 12	L-out (L-ch output) R-out (R-ch output)	(1/12) GND2 (8)	1.35	1.35	

4

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
NO.			AM	FM	
13	VCO	V _{CC2} (S) (13) (GND2 (8)	5.0	4.1	
14	LPF2 • LPF terminal for synchronous detector. • VCO stop terminal V ₁₄ = GND → VCO stop	GND2 8	5.0	3.4	
15	LPF1 • LPF terminal for phase detector • Bias terminal for AM / FM SW circuit V ₁₅ = GND → AM V ₁₅ = open → FM	GND2 8	0	2.8	
16	FM ST DET in	(B) M M M M M M M M M M M M M M M M M M M	1.4	1.4	

Pin No.	Characteristic	Characteristic Internal Circuit						
17	DET out	VCC2 (5) AM OFM FM 17) (B) (B) (COM) (AM 1.4	FM 1.4				
18	IF out / REQ $V_{18} = GND \rightarrow IF$ out	\$\footnote{VCC2}	4.0	4.0				
19	OSC out	AM OSC FM OSC 2 GND1						
20	V _{CC1} (V _{CC} for RF stage)	-	5.0	5.0				
21	FM OSC	V _{CC1} 20 21 MIX - II GND1 2	5.0	5.0				

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal) AM FM		
			Alvi	1 IVI	
22	AM OSC	22	5.0	5.0	
23	FM RF out	cf. pin (1)	5.0	5.0	
24	AM RF in	V _{CC1} 20 AGC 24 GND2 2	5.0	5.0	

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V _{CC}	15	V
LED current	I _{LED}	10	mA
LED voltage	V_{LED}	15	V
Power dissipation	P _D *	1200	mW
Operating temperature	T _{opr}	-25~75	°C
Storage temperature	T _{stg}	−55~150	°C

^{*:} Derated above Ta = 25°C in the proportion of 9.6mW / °C

Electrical Characteristics

Unless Otherwise Specified, Ta = 25°C, V_{CC} = 5V, SW8: Off, F / E: f = 98MHz, f_m = 1kHz FM IF: f = 10.7MHz, Δf = ±22.5kHz, f_m = 1kHz

AM: f = 1MHz, MOD = 30%, $f_m = 1kHz$ FM ST DET: $f_m = 1kHz$

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit	
Sunni	y current	I _{CC (FM)}	_	— V _{in} = 0, FM mode		27	36	mA	
Зиррі	y current	ICC (AM)	ı	V _{in} = 0. AM mode	_	18	25	IIIA	
. / E	Input limiting voltage	V _{in} (lim)		–3dB limiting with respect to V _{OD} level at Vin = 60dBμV EMF		11	-	dBµV EMF	
ш	Local OSC buffer output voltage	V _{OSC} (buff) FM	_	f _{OSC} = 108.7MHz	90	180	_	mV _{rms}	
	Input limiting voltage V_{in} (lim.) IF $ -3dB$ limiting with respect to V_{OD} level at V_{in} = 80dB μ V EMF		40	45	50	dBµV EMF			
	Recovered output voltage	V _{OD}	1	V _{in} = 80dBμV EMF	50	75	100	mV _{rms}	
	Signal to noise ratio	S/N	_	V _{in} = 80dBμV EMF	_	70	_	dB	
	Total harmonic distortion	THD	— V _{in} = 80dBμV EMF			0.3	_	%	
FM IF	AM rejection ratio	AMR	_	V _{in} = 80dBμV EMF	_	50	_	dB	
	SD output sensitivity	V _{SD}	V _{SD} — V _{SD} = V _{CC} -0.1V		53	58	63	dBµV EMF	
	IF count output frequency	f1 / 8 IF (FM)	_	V _{in} = 80dBμV EMF, SW8: On	1.3373	1.3375	1.3377	MHz	
	IF count output voltage	V1 / 8 IF (FM)	_	V _{in} = 80dBμV EMF,SW8: On	350	500	_	$mV_{p\!-\!p}$	
	IF count output sensitivity	IF sens (FM)	_	SW8: On	49	54	59	dBµV EMF	

8

	Characteris	stic	Symbol	Test Cir– cuit	Test Condi	tion	Min.	Тур.	Max.	Unit
	Gain		G_V	ı	V _{in} = 26dBµV EMF		20	45	80	mV _{rms}
	Recovered output voltage		V _{OD}	_	V _{in} = 60dBμV EMF		45	65	90	mV _{rms}
	Signal to nois	se ratio	S/N	-	V _{in} = 60dBµV EMF			42	_	dB
AM	Total harmon distortion	nic	THD	_	V _{in} = 60dBμV EMF		_	1.0	_	%
4	Local OSC b output voltag		V _{OSC} (buff) AM	_	f _{OSC} = 1.45MHz		90	150	_	mV _{rms}
	IF count outp voltage	ut	V _{IF} (AM)	_	V _{in} = 60dBμV EMF, SW8: On,		350	500	_	mV_{p-p}
	IF count outp sensitivity	ut	IF sens (AM)	_	SW8: On		35	40	45	dBµV EMF
Din (1	7) output rocio	stance	D17		FM mode		_	0.75	_	kΩ
PIII (1	r) output resis	output resistance R17 — AM mode			_	15.5	_	K77		
	Input resistar	nce	R _{IN}	-			_	24	_	kΩ
	Output resistance		R _{OUT}	-			_	5	_	kΩ
	Max. Composite signal input voltage		V _{in max} (stereo)	_	L + R = 90%, P = 10%, SW4: LPF on f _m = 1kHz, THD = 3%		_	800	_	mV _{rms}
					L + R = 180mV _{rms}	f _m = 100Hz	-	42	-	dB
	Separation		Sep.	_	$P = 20mV_{rms}$	f _m = 1kHz	35	42	ı	
					SW4: LPF on	f _m = 10kHz	1	42	1	
 	Total harmonic	Monaural	THD (monaural)		V _{in} = 200mV _{rms}		_	0.1	_	%
FM St DET	distortion	Stereo	THD (stereo)		L + R = 180mV _{rms} , P = 20mV _{rms} , SW4: LPF on,		-	0.1	-	76
Ē	Voltage gain		G _V	-	V _{in} = 200mV _{rms}		-2	0	2	dB
	Channel bala	ince	C. B.	_	V _{in} = 200mV _{rms}		-2	0	2	dB
	Stereo LED	On	V _{L (ON)}		Pilot input		_	8	15	- mV _{rms}
	sensitivity	Off	V _{L (OFF)}	-	Pilot iriput		2	6	_	
	Stereo LED h	nysteresis	V _H	_	To LED turn off from LED turn on		-	2	-	mV _{rms}
	Capture rang	е	C. R.	-	P = 15mV _{rms}		_	±1.3	_	%
	Signal to nois	se ratio	S/N	_	V _{in} = 200mV _{rms}		_	80	_	dB
	Muting attenu	uation	MUTE	_	V _{in} = 200mV _{rms}		_	80	_	dB

TEST CIRCUIT

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Coil Data

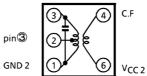
Coil No.	Test Freq.	L (µH)	C _o (pF)	Qo	1–2	Tu 2–3	rns 1–3	3–6	Wire (mm _{\$\phi\$})	Reference
L1 FM RF	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
L1 FM OSC	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
T1 AM mix	455kHz		180	48↑	47	111	158	4–6 20	0.06 UEW	(T): A7LCS-12064N
T2 AM OSC	796kHz	268		125	15	89			0.06 UEW	(S): 2157–2239–213A (T): A7BRS–11998Y

(S): Sumida electric co., Itd.

T2: AM OSC

(T): Toko co., Itd.

 $\begin{array}{c} \mathsf{L}_1 \,:\, \mathsf{FM} \;\; \mathsf{RF} \\ \mathsf{L}_2 \,:\, \mathsf{FM} \;\; \mathsf{OSC} \end{array}$



T1: AM MIX

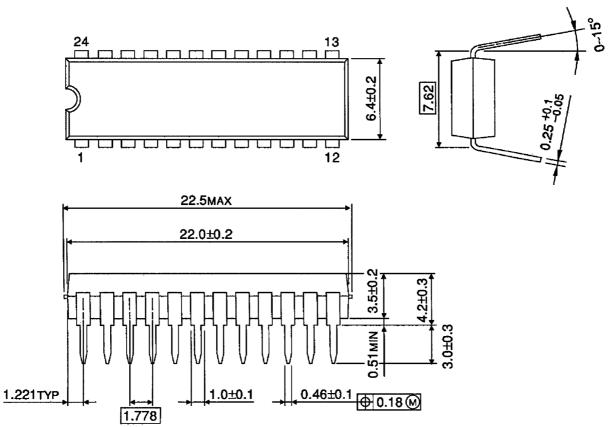
V.C pin 🕸

V_{CC} 1



Package Dimensions

SDIP24-P-300-1.78 Unit: mm



12

Weight: 1.2g (typ.)

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000707EBA

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